

## SEMICONDUCTOR THIN FILM AND MANUFACTURE THEREOF

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Patent Number: JP2000353666

Publication  
date: 2000-12-19

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Requested  
Patent: ☐ JP2000353666

Application  
Number: JP19990164889 19990611

Priority  
Number(s):

IPC  
Classification: H01L21/205; H01L21/20; H01L29/786; H01L21/336

EC  
Classification:

EC  
Classification:

Equivalents:

### Abstract

**PROBLEM TO BE SOLVED:** To form a crystalline silicon film at a low temperature by forming an atomic layer and a layer, having a peak concentration of a catalyst element around an interface between a substrate and a semiconductor thin film, and subsequently made to contain the catalyst element in and outside the semiconductor thin film.

**SOLUTION:** On a glass substrate 1, a coating 2 made of a material such as silicon oxide is formed through sputtering method, and then a semiconductor thin film 3 such as a crystalline silicon film is formed thereon. Subsequently, around an interface 4 between the substrate 1 and the semiconductor thin film 3, an atomic layer is formed, which contains a catalyst element for accelerating the growth of a crystal. Furthermore, a layer having a peak concentration of the catalyst element is formed around the interface 4 between the substrate 1 and the semiconductor thin film 3, and the catalyst element is contained in and outside the semiconductor thin film 3. Therefore, it is possible to manufacture a semiconductor thin-film device, such as a low-temperature forming thin-film transistor having high performance.